PROCESS FOR TRANSFER OF A THIN LAYER FORMED IN A SUBSTRATE WITH VACANCY CLUSTERS

ABSTRACT OF THE DISCLOSURE

According to a first aspect the invention relates to a process for making a substrate comprising a thin layer of semiconducting material and a support substrate, the thin layer resulting from the transfer to the support substrate of a part of a donor substrate with vacancy clusters at a first density, characterised in that it comprises:

- after transfer of said part of the donor substrate to the support substrate, a curing step of the vacancy clusters present in the part of the donor substrate transferred onto the support substrate to reduce the first density to a second density;
- and before the said curing step, one or several steps adapted so as not to increase the size of the vacancy clusters present in said part of the support substrate at said first density.

The invention also relates to a SeOI substrate obtained by this process, and a process for recycling a substrate with vacancy clusters and having been used as a donor substrate from which a thin layer was taken and transferred onto a support substrate.

Figure 1